

# Exploring GaN crystallographic orientation disparity and its origin on bare and partly graphene-covered $m$ -plane sapphire substrates

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## Abstract

The crystallographic orientation of 3D materials grown over 2D material-covered substrates is one of the critical factors in discerning the true growth mechanism among competing possibilities, including remote epitaxy, van der Waals epitaxy, and pinhole-seeded lateral epitaxy also known as thru-hole epitaxy. However, definitive identification demands meticulous investigation to accurately interpret experimentally observed crystallographic orientations, as misinterpretation can lead to mistaken conclusions regarding the underlying growth mechanism. In this study, we demonstrate that GaN domains exhibit orientation disparities when grown on both bare and partly graphene-covered  $m$ -plane sapphire substrates. Comprehensive measurements of crystallographic orientation unambiguously reveal that GaN domains adopt (100) and (103) orientations even when grown under identical growth conditions on bare and partly graphene-covered  $m$ -plane sapphire substrates, respectively. Particularly, high-resolution transmission electron microscopy unequivocally establishes that GaN grown over partly graphene-covered  $m$ -plane sapphire substrates started to nucleate on the exposed sapphire surface. Our research elucidates that crystallographic orientation disparities can arise even from thru-hole epitaxy, challenging the commonly accepted notion that such disparities cannot be attributed to thru-hole epitaxy when grown under identical growth conditions.

## I. INTRODUCTION

To date, the true growth mechanism of remote epitaxy has been a subject of ongoing debate. Initially, it was proposed that remote epitaxy relied on the remote influence of the substrate potential through an ultrathin 2D material<sup>1</sup>. However, conflicting reports have emerged, where experimental results, such as the crystallographic alignment of grown domains over the 2D material and the facile detachment of these domains, were equally well reproduced when epitaxial lateral overgrowth occurred through small holes in the 2D material although those results were named differently as thru-hole epitaxy<sup>2,3</sup> or pinhole-seeded lateral epitaxy<sup>4</sup>. Furthermore, calculations based on density functional theory suggested that the potential due to the substrate through the 2D material was not only negligibly small but also did not reflect the symmetry of the bare substrate. This raised questions about whether “remoteness” is indeed the true growth mechanism of remote epitaxy. Experimentally determining the genuine growth mechanism of remote epitaxy has proven to be a non-trivial task, and as of now, there is no experimental evidence definitively disproving the idea of “remoteness” as the true growth mechanism in remote epitaxy.

In a recent study, GdPtSb films exhibited differing preferred orientations when grown on bare sapphire substrates compared to holey-graphene-covered sapphire substrates, despite identical growth conditions.<sup>5</sup> The authors of that study highlighted that holey-graphene-covered sapphire substrates exposed fractions of the underlying sapphire surface due to inherent openings or holes in the graphene layer. Among the potential growth mechanisms considered (remote epitaxy and pinhole-seeded lateral epitaxy), the authors excluded pinhole-seeded lateral epitaxy from a probable mechanism. They reasoned that it was unlikely for GdPtSb to exhibit orientation disparity solely based on the areal fraction of exposed surface (bare vs. holey-graphene-covered) under identical growth conditions. The implicit assumption was that dissimilar preferred orientations would not occur when grown under identical growth conditions if the material nucleated on the exposed sapphire substrate, regardless of the exposed area’s size. Consequently, the authors attributed the dissimilar preferred orientation when grown on holey graphene, to remote epitaxy. However, they acknowledged that eliminating the competing mechanism (pinhole-seeded lateral epitaxy) did not definitively prove the existence of remote epitaxy.

In light of the logical progression and conclusions drawn in the aforementioned paper, a

critical question emerges: Can domains grown on a holey-graphene-covered substrate when directly nucleated on the exposed area of a substrate have dissimilar orientations to those grown under identical growth conditions on a bare substrate? As mentioned earlier, the exclusion of pinhole-seeded lateral epitaxy from a probable growth mechanism was based on the implicit assumption that domains nucleated on the exposed areas of the substrate would have the same preferred orientation as those grown on a bare substrate under identical growth conditions. If this holds true, it logically follows that domains in the pinhole-seeded lateral epitaxy regime would exhibit similar preferred orientations to those on a bare substrate under identical growth conditions, as the fraction of opening areas increases.

In our study, we conducted the growth of GaN on two different substrates: a bare  $m$ -plane sapphire substrate and a partly graphene-covered  $m$ -plane sapphire substrate, in which the fractional area of openings was intentionally set to be much higher than that of the holey-graphene-covered sapphire substrate examined in the previous paper<sup>5</sup>. Our results demonstrate that the preferred orientation of domains grown on the bare and partly graphene-covered substrates can indeed differ when subjected to pinhole-seeded epitaxy under identical growth conditions. Consequently, pinhole-seeded epitaxy cannot be definitively excluded from a possible growth mechanism responsible for dissimilar preferred orientations observed when growing on either bare or graphene-covered substrates.

Furthermore, the attribution of dissimilar preferred orientations to remote epitaxy in the previous paper<sup>5</sup> appears somewhat inconsistent with typical experimental results associated with remote epitaxy. This inconsistency arises because, in the regime of remote epitaxy, there is no dissimilarity in preferred orientations observed when a film is grown on both bare substrates and 2D-material-covered substrates, primarily due to the negligibly small contribution from the 2D material to the film's growth. In fact, the transparency of 2D material from the perspective of epitaxial growth constitutes a fundamental aspect of the concept of remote epitaxy.

## II. EXPERIMENTAL METHODS

Graphene was directly grown by chemical vapor deposition on an  $m$ -plane sapphire substrate with the temperature of 1050 °C, the pressure of 400 torr, the flow rate of Ar, CH<sub>4</sub> and H<sub>2</sub> was 600 sccm, 15 sccm and 10 sccm, respectively. The growth time of graphene was 3

hours. GaN was grown on bare  $m$ -plane sapphire (substrate I) and partly graphene-covered  $m$ -plane sapphire (substrate II) by hydride vapor phase epitaxy. The substrate temperature was 945 °C, and the flow rate of NH<sub>3</sub> and HCl was 600 sccm and 4 sccm, respectively. The growth time of GaN was 3 minutes.

In this study, GaN growth was carried out without the use of a low-temperature buffer layer, which is typically employed to achieve a continuous and flat GaN film. Instead, GaN was grown in the form of isolated domains, allowing for a direct assessment of the preferred orientation of these domains through visual inspection using scanning electron microscopy<sup>2</sup>. Additionally, X-ray diffraction analysis was performed to confirm the preferred orientation of GaN domains, whether they were grown on graphene/ $m$ -plane sapphire or on bare  $m$ -plane sapphire surfaces. The AFM topography images were obtained using the Park Systems XE-100 AFM at the Multi-Dimensional Material Convergence Research Center at Kyung Hee University.

### III. RESULTS AND DISCUSSION

To conduct a comparative investigation into the impact of a partially covering graphene substrate, serving as a mask layer, on the crystallographic orientation of GaN when grown on  $m$ -plane sapphire, we prepared a graphene/ $m$ -plane sapphire substrate by directly growing graphene on the  $m$ -plane sapphire substrate.

In Fig.1 (a), we present the AFM topography along with a line profile of the graphene directly grown on an  $m$ -plane sapphire substrate. Here, approximately one-nanometer-thick round-shaped domains are densely distributed across the substrate, resulting in an estimated areal coverage of graphene of approximately 45%, as determined by ImageJ analysis. Notably, the graphene domains only partly cover the  $m$ -plane sapphire substrate. This intentional control of graphene's areal coverage was designed to ensure that a substantial portion of the  $m$ -plane sapphire substrate remained exposed, providing ample nucleation sites for the subsequently grown GaN. Consequently, the areal coverage of graphene in our sample is considerably smaller than that of holey graphene as utilized in the previous study<sup>5</sup>. Raman spectra, as depicted in Fig.1 (b), confirm that these domains consist of a few-layer-thick graphene<sup>6</sup>, consistent with the thickness measurement obtained from the AFM line profile.

Two  $m$ -plane sapphire substrates were prepared, with one (substrate I) left bare and the

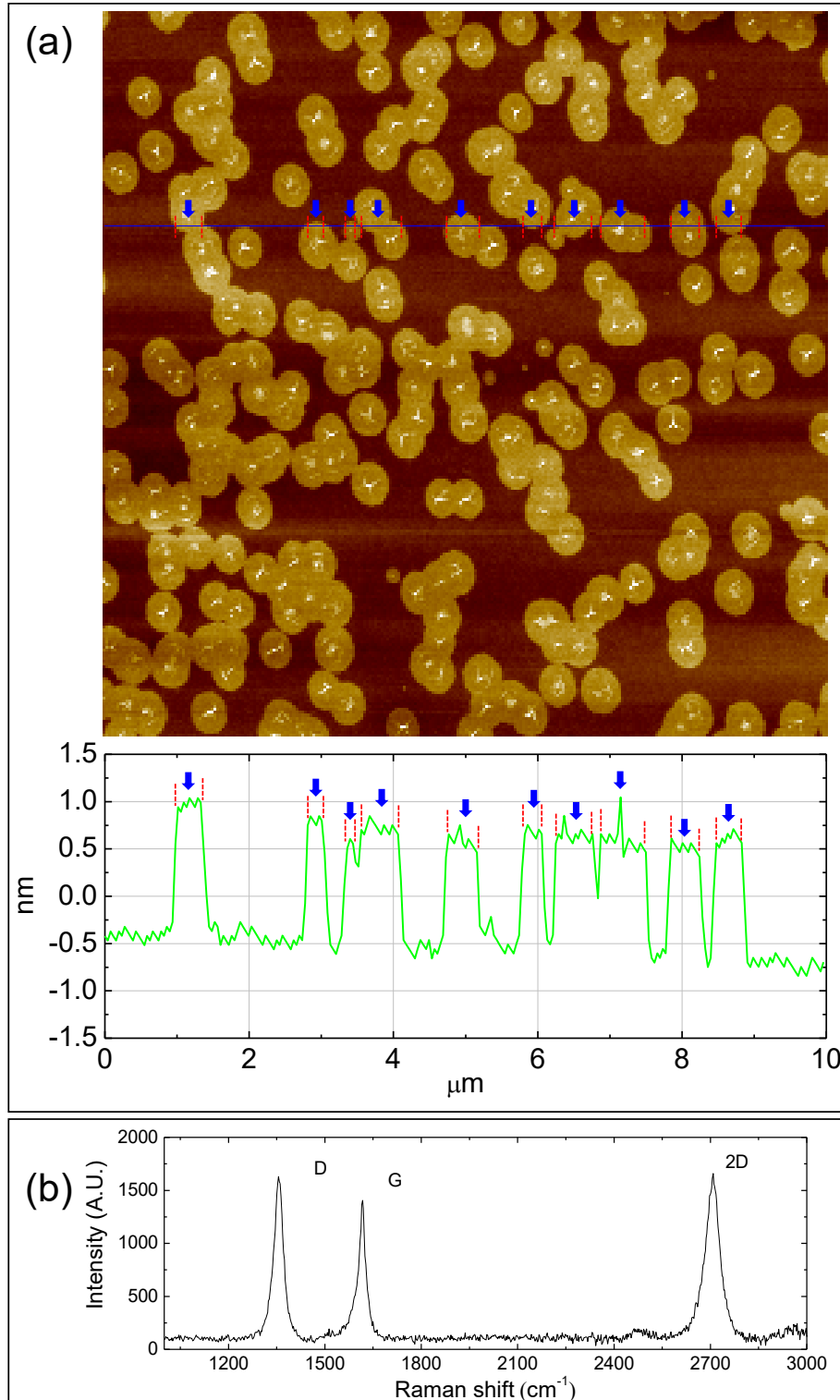


FIG. 1. (a) AFM topography of graphene directly grown on an  $m$ -plane sapphire substrate. Shown below is a height profile of graphene/ $m$ -plane sapphire along the blue line. (b) Raman spectroscopy of graphene grown on  $m$ -plane sapphire substrate (substrate II).

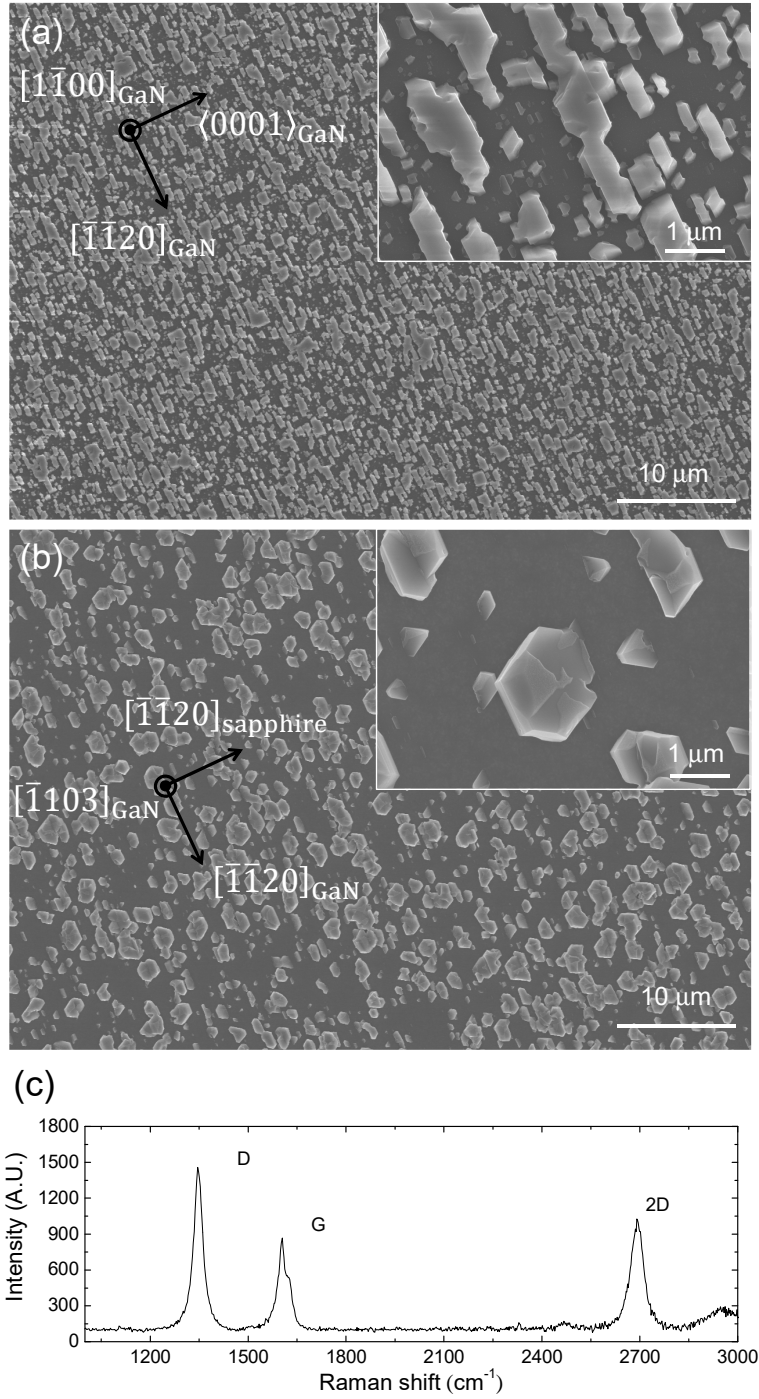


FIG. 2. SEM images of GaN domains grown on (a) a bare *m*-plane sapphire or (b) a partly graphene-covered *m*-plane sapphire substrate. The characteristic shapes of GaN domains on substrate I and II are associated with (100)- and (103)-oriented domains, respectively. (c) Raman spectroscopy of graphene after GaN was grown on a partly graphene-covered *m*-plane sapphire substrate (substrate II).

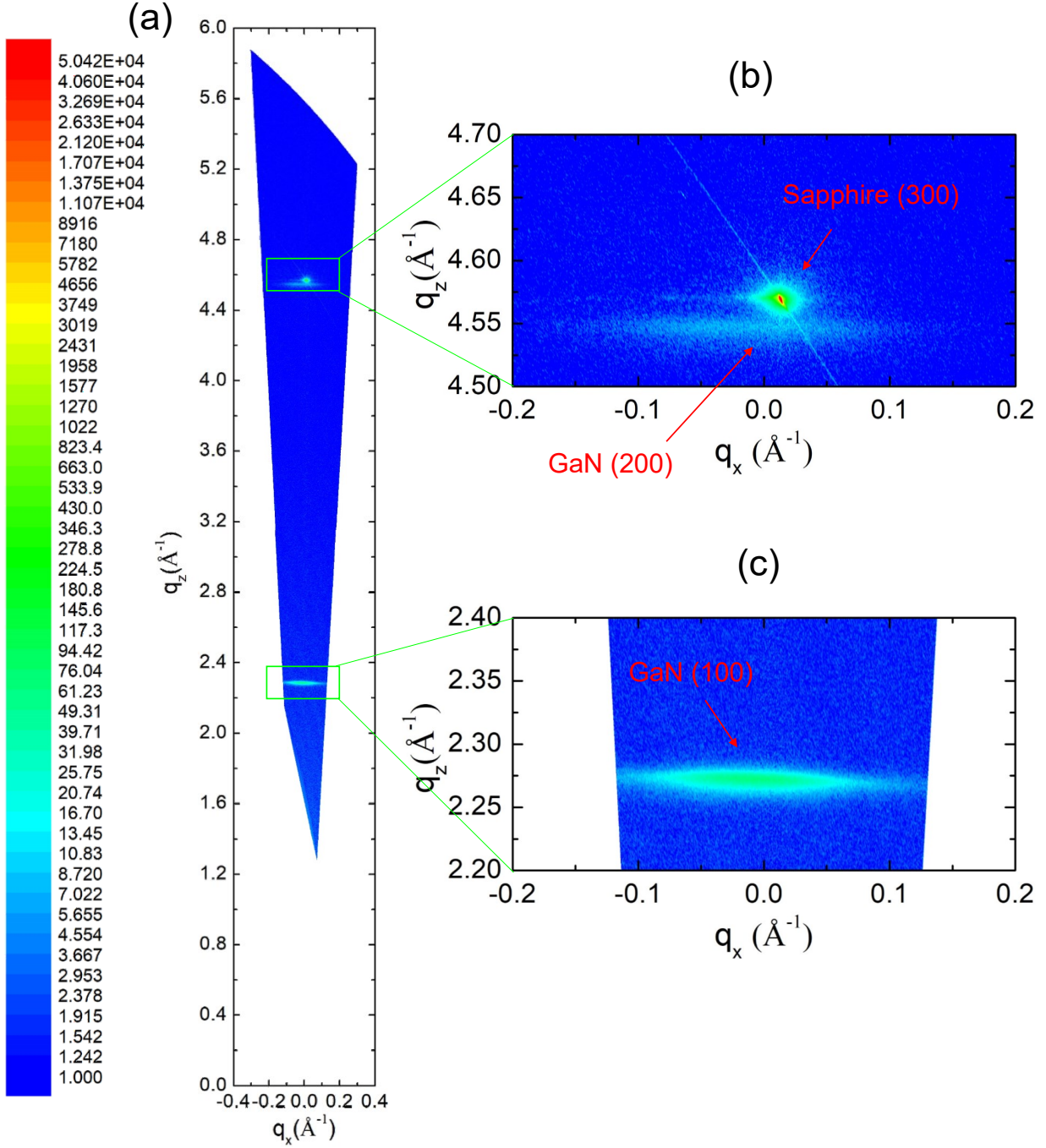


FIG. 3. (a) The reciprocal space map of X-ray diffraction of GaN grown on substrate I. (b)~(c) Magnified reciprocal space maps clearly show that (100) Bragg peak at  $q_z = 2.270 \text{ \AA}^{-1}$  and (200) Bragg peak at  $q_z = 4.547 \text{ \AA}^{-1}$  are the only Bragg peaks of GaN observed when grown on substrate I. Of course, sapphire (300) Bragg peak at  $q_z = 4.570 \text{ \AA}^{-1}$  is also seen.



other (substrate II) having graphene partly grown on it. Both substrates were subjected to GaN growth under identical conditions. As illustrated in Fig.2, scanning electron microscopy (SEM) images were captured for each of the two samples. Given that a low-temperature buffer layer was not employed, GaN was grown as isolated islands with well-defined facets rather than forming a continuous film. Visual inspection immediately revealed that the preferred orientation of the GaN domains grown on the two substrates was dissimilar. To be more specific, the domain shapes in Fig.2(a) and (b) exhibited characteristic features associated with (100)- and (103)-oriented GaN domains, respectively<sup>3,7-12</sup>. A more rigorous analysis of the crystallographic orientation of the grown GaN domains is given later using X-ray diffraction.

To ascertain whether the graphene layer, directly grown on *m*-plane sapphire, remained intact during the subsequent GaN growth on substrate II, we conducted Raman spectroscopy measurements. The Raman measurement in fig. 2(c) revealed that the graphene remained robust, exhibiting no significant damage during the GaN growth process. This observation aligns with previously reported findings regarding the stability of graphene on sapphire substrates while the damage of graphene on III-nitrides was observed at temperatures above the nitride decomposition threshold.<sup>13-15</sup>

Additionally, we conducted reciprocal space maps (RSMs) of X-ray diffraction for GaN grown on both substrate I and II to provide rigorous confirmation of the crystallographic orientation of GaN. As depicted in Fig. 3, the RSM for GaN grown on the bare *m*-plane sapphire substrate (substrate I) displays (100) and (200) Bragg peaks, unequivocally confirming that GaN on this substrate exclusively exhibits (100)-orientation.

Conversely, Fig. 4 reveals a different scenario for substrate II, where the RSM exhibits a (103) Bragg peak that is split into two components. This result indicates that GaN grown on *m*-plane sapphire with a graphene areal fraction less than unity predominantly possesses a (103)-orientation. It's worth noting that the apparent splitting of the (103) Bragg peak is attributable to the tilting of two variants in opposite directions, as previously reported<sup>8</sup>, and is not due to potential fluctuations caused by graphene. The observed tilt angle for each variant is approximately  $\sim 1.7^\circ$ , consistent with the previously reported tilt angle of  $\sim 2.0^\circ$ .<sup>8</sup>

The next question we aimed to answer is whether the dissimilarly oriented GaN domains originated from nuclei with differing orientations on the exposed areas of each *m*-plane sapphire substrate. To address this matter, we conducted high-resolution cross-sectional trans-

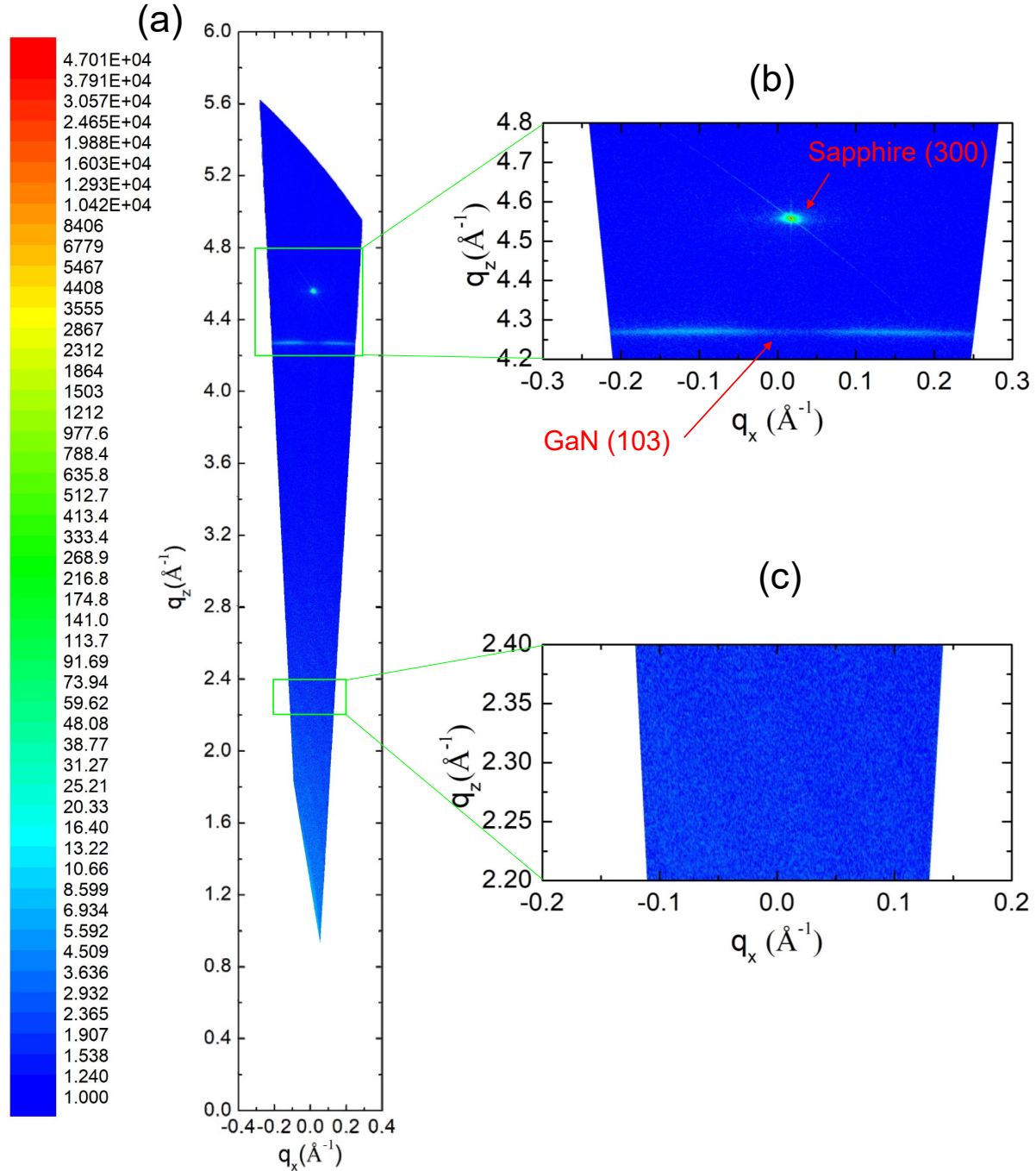


FIG. 4. The reciprocal space map of X-ray diffraction of GaN grown on substrate II. (b)~(c) Magnified reciprocal space maps clearly show that (103) Bragg peak at  $q_z = 4.270 \text{ \AA}^{-1}$  is the only Bragg peak of GaN observed when grown on substrate II while sapphire (300) Bragg peak at  $q_z = 4.570 \text{ \AA}^{-1}$  is of course observed. GaN (103) Bragg peak is split because of the slight tilt of twins in opposite directions.<sup>8</sup> Note that neither (100) nor (200) GaN Bragg peak is observed when grown on substrate II.

mission electron microscopy (TEM). As illustrated in Fig. 5, both (100)- and (103)-oriented GaN were found to be in direct contact with the  $m$ -plane sapphire substrate, indicating that two dissimilarly oriented GaN domains nucleated under the same growth conditions on two  $m$ -plane sapphire substrates (one bare and the other partly covered with graphene) placed within the same reactor. Notably, the areal fraction of graphene, as shown in the AFM topography, is much less than unity, and graphene is not observed in the high-resolution cross-sectional TEM image. Therefore, this result unequivocally demonstrates that dissimilarly oriented domains can nucleate on the same substrate with different graphene coverages (0 and 0.45, respectively), despite the absence of any influence from the potential supposedly induced by graphene. Consequently, the presence of dissimilarly oriented domains cannot be attributed solely to the modified potential?i.e., the superposed potential from both graphene and  $m$ -plane sapphire.

All experimental results, including those from SEM, XRD, and TEM, consistently demonstrate differences in the crystallographic orientation of GaN when grown on  $m$ -plane sapphire, with or without the presence of graphene. Notably, in the case of GaN growth on substrate II, GaN initially nucleated on the exposed  $m$ -plane sapphire substrate before laterally growing over graphene, rather than the other way around. Consequently, TEM results clearly suggest that GaN can exhibit varying crystallographic orientations when grown on the same  $m$ -plane sapphire substrate under identical growth conditions, depending on whether the substrate is partly covered by graphene as a mask material. This phenomenon cannot be attributed to GaN with varying crystallographic orientations being nucleated on graphene due to a modified substrate potential, as previously suggested.<sup>5</sup> Instead, it arises from GaN with different crystallographic orientations directly nucleating on  $m$ -plane sapphire.

To explore the cause of this orientation disparity, we can draw valuable insights from our prior publication. In a previous study, we reported that GaN exhibited dissimilar preferred orientations when grown on SiO<sub>2</sub>-patterned  $m$ -plane sapphire with variations in hole sizes and separations.<sup>10</sup> Our results in this work suggest that the orientation disparity of GaN on  $m$ -plane sapphire is not unique to graphene masking but also occurs with SiO<sub>2</sub> masking. Furthermore, our previous research indicated that the (100) preferred orientation was more favored over (103) as the fractional ratio of an opening area increased, a finding consistent with the results presented in this work. In our previous paper, we revealed that the effective concentration of species reaching the exposed substrate, which was related to the fractional

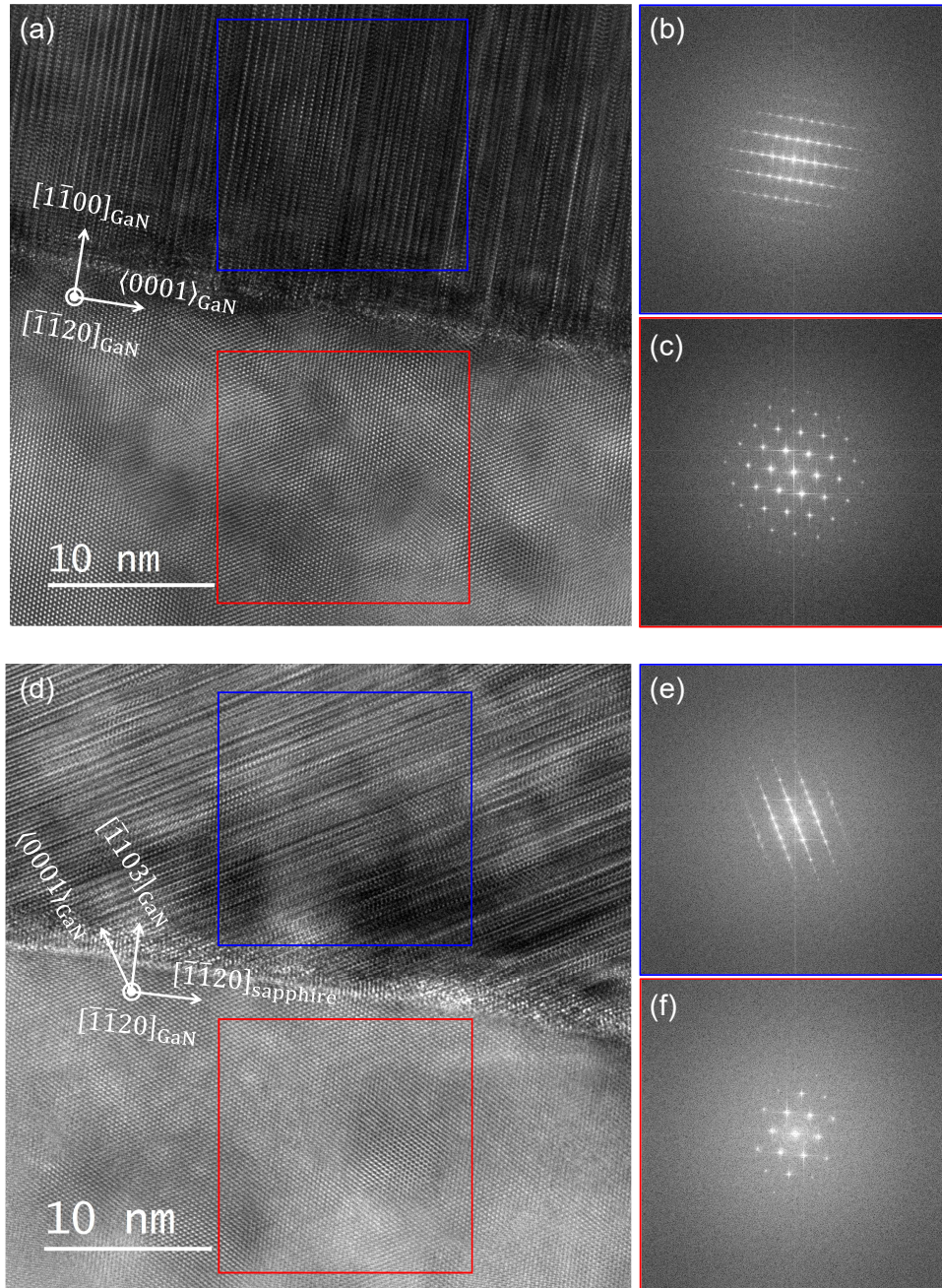


FIG. 5. High-resolution cross-sectional TEM image of the interfacial region between GaN and *m*-plane sapphire for the case when grown on (a) substrate I and (d) substrate II, respectively. FFT of the GaN and sapphire regions marked by blue and red squares are shown in (b) and (c) for case I and (e) and (f) for case II, respectively.

ratio of an opening area, played a role in determining the crystallographic orientation, as supported by density functional theory calculations.<sup>10</sup>

This intriguing observation decisively confirms that the crystallographic orientation is not solely determined once the film material and substrate material are selected. Previously, the crystallographic orientation of GaN when grown on bare *m*-plane sapphire substrates was observed to vary depending on the growth conditions,<sup>9</sup> but in this work, we showed that the orientation disparity can be also observed under identical growth conditions on bare and partly graphene-covered *m*-plane sapphire substrates. In other words, factors such as growth conditions and mask coverage also play a significant role in determining the preferred crystallographic orientation of the material when directly nucleated on the substrate. This result contradicts the assumption made in the previous paper that dissimilar crystallographic orientations cannot result from pinhole-seeded lateral epitaxy<sup>5</sup>. Of course, there are situations in which mask coverage does not cause orientation disparity of GaN, particularly when grown on *c*-plane sapphire substrates. The effect of growth conditions and mask coverage on the orientation disparity is not universal and valid in a limited situation. However, the observation of thru-hole epitaxy responsible for orientation disparity is sufficient enough to serve as counter-evidence to the role of remote epitaxy exclusively considered responsible for the orientation disparity in the aforementioned paper.<sup>5</sup>

#### IV. CONCLUSION

In summary, our observations reveal distinct preferred orientations of GaN domains: (100) orientation on bare *m*-plane sapphire and (103) orientation on partly graphene-covered *m*-plane sapphire, both grown under identical conditions. TEM analysis provides unequivocal evidence that these domains nucleate directly on both bare and partly graphene-covered *m*-plane sapphire substrates. This finding suggests that dissimilar crystallographic orientations can occur even when the material is directly nucleated on the exposed substrate surface, without the need for a superposed potential due to 2D materials covering the substrate. In general, various factors, including growth conditions and mask coverage, can influence the crystallographic orientation of materials grown on a substrate, even when directly nucleated on the exposed surface of a substrate.

Importantly, our research findings challenge and refute the claims made by Du et al. in

their published paper.<sup>5</sup> In contrast to their assertion that remote epitaxy is the exclusive cause of dissimilar preferred orientations in films grown on graphene-covered substrates, our findings indicate that thru-hole epitaxy can also be the origin of orientation disparity. These dissimilar orientations of GaN domains not only expand our understanding of crystal growth mechanisms but also underscore the importance of careful consideration when identifying the true growth mechanism of 3D materials over 2D materials based on the crystallographic orientation of the 3D materials.

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